J108, J109 N-Channel JFET

Features

- InterFET N0450S Geometry
- Low Noise: 1 nV/√Hz Typical
- High Gain: 100mS Typical
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

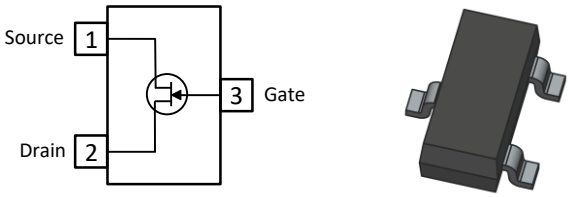
Applications

- Choppers
- Commutators
- Analog Switches

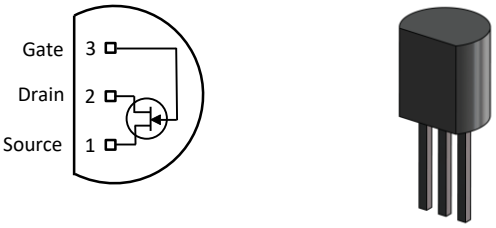
Description

The -25V InterFET J108 and J109 JFET's are targeted for high gain low noise switching, commutator, and chopper applications.

SOT23 Top View



TO-92 Bottom View



Product Summary

Parameters		J108 Min	J109 Min	Unit
BV_{GSS}	Gate to Source Breakdown Voltage	-25	-25	V
I_{DSS}	Drain to Source Saturation Current	80	40	mA
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-3	-2	V

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
J108; J109	Through-Hole	TO-92	Bulk
SMPJ108; SMPJ109	Surface Mount	SOT23	Bulk
SMPJ108TR; SMPJ109TR	7" Tape and Reel: Max 3,000 Pieces 13" Tape and Reel: Max 9,000 Pieces	SOT23	Minimum 1,000 Pieces Tape and Reel
J108COT; J109COT	Chip Orientated Tray (COT Waffle Pack)	COT	400/Waffle Pack
J108CFT; J109CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack

Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

Parameters		Value	Unit
V_{RGS}	Reverse Gate Source and Gate Drain Voltage	-25	V
I_{FG}	Continuous Forward Gate Current	50	mA
P_D	Continuous Device Power Dissipation	360	mW
P	Power Derating	3.27	mW/°C
T_J	Operating Junction Temperature	-55 to 125	°C
T_{STG}	Storage Temperature	-65 to 200	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

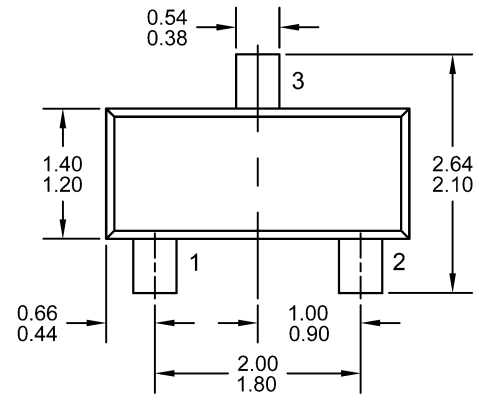
Parameters		Conditions	J108		J109		Unit
			Min	Max	Min	Max	
$V_{(BR)GSS}$	Gate to Source Breakdown Voltage	V_{DS} = 0V, I_G = -1µA	-25		-25		V
I_{GSS}	Gate to Source Reverse Current	V_{GS} = -15V, V_{DS} = 0V		-3		-3	nA
$V_{GS(OFF)}$	Gate to Source Cutoff Voltage	V_{DS} = 5V, I_D = 1µA	-3	-10	-2	-6	V
I_{DSS}	Drain to Source Saturation Current	V_{GS} = 0V, V_{DS} = 15V (Pulsed)	80		40		mA
I_D	Drain Cutoff Current	V_{DS} = 5V, V_{GS} = -10V		3		3	nA

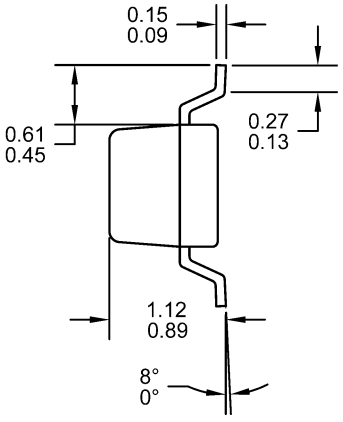
Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

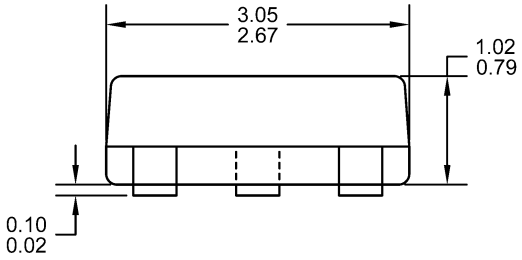
Parameters		Conditions	J108		J109		Unit
			Min	Max	Min	Max	
$R_{DS(ON)}$	Drain to Source ON Resistance	V_{DS} <= 0.1V, V_{GS} = 0V, f = 1kHz		8		12	Ω
C_{gd}	Drain Gate Capacitance	V_{DS} = 0V, V_{GS} = -10V, f = 1MHz		15		15	pF
C_{gs}	Input Capacitance	V_{DS} = 0V, V_{GS} = -10V, f = 1MHz		15		15	pF
$C_{gd} + C_{gs}$	Drain + Source Gate Capacitance	V_{DS} = V_{GS} = 0V, f = 1MHz		85		85	pF
$t_{d(ON)}$	Turn ON Delay Time	V_{DD} = 1.5V, R_L = 150 Ω J108: $V_{GS(OFF)}$ = -12V J109: $V_{GS(OFF)}$ = -7V	3 (typ)		3 (typ)		ns
t_r	Rise Time		1 (typ)		1 (typ)		ns
$t_{d(OFF)}$	Turn OFF Delay Time		4 (typ)		4 (typ)		ns
t_f	Fall Time		18 (typ)		18 (typ)		ns

SOT23 (TO-236AB) Mechanical and Layout Data

Package Outline Data

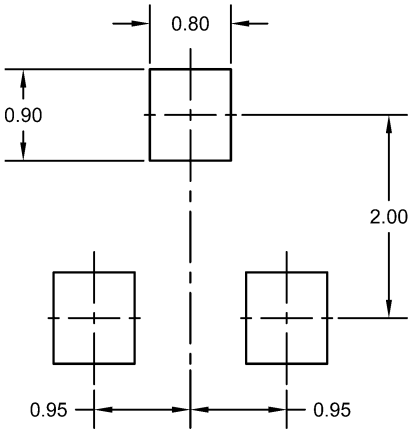






1. All linear dimensions are in millimeters.
2. Package weight approximately 0.12 grams
3. Molded plastic case UL 94V-0 rated
4. For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
5. Bulk product is shipped in standard ESD shipping material
6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.